Switch Mode Power Rectifiers

These state-of-the-art devices have the following features:

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage Drop
- 150°C Operating Junction Temperature
- Wettable Flacks Option Available
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94–0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

Applications

- Output Rectification in Compact Portable Consumer Applications
- Freewheeling Diode used with Inductive Loads



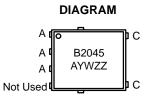
ON Semiconductor®

www.onsemi.com

SCHOTTKY BARRIER RECTIFIERS 20 AMPERES 45 VOLTS







MARKING

B2045 = Specific Device Code A = Assembly Location

Y = Year W = Work Week ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR2045MFST1G	SO-8 FL (Pb-Free)	1500 / Tape & Reel
NRVB2045MFST1G*	SO-8 FL (Pb-Free)	1500 / Tape & Reel
MBR2045MFST3G	SO-8 FL (Pb-Free)	5000 / Tape & Reel
NRVB2045MFST3G*	SO-8 FL (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	V _{RRM} V _{RWM}	45	V
DC Blocking Voltage	V _R	45	
Average Rectified Forward Current (Rated V_R , $T_C = 130$ °C)	l _{F(AV)}	20	A
Peak Repetitive Forward Current, (Rated V _R , Square Wave, 20 kHz, T _C = 135°C)	I _{FRM}	40	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	400	А
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature	TJ	-55 to +150	°C
Unclamped Inductive Switching Energy (10 mH Inductor, Non-repetitive)	E _{AS}	150	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		M4	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

NOTE: The heat generated must be less than the thermal conductivity from Junction-to-Ambient: dPD/dTJ < 1/RJA

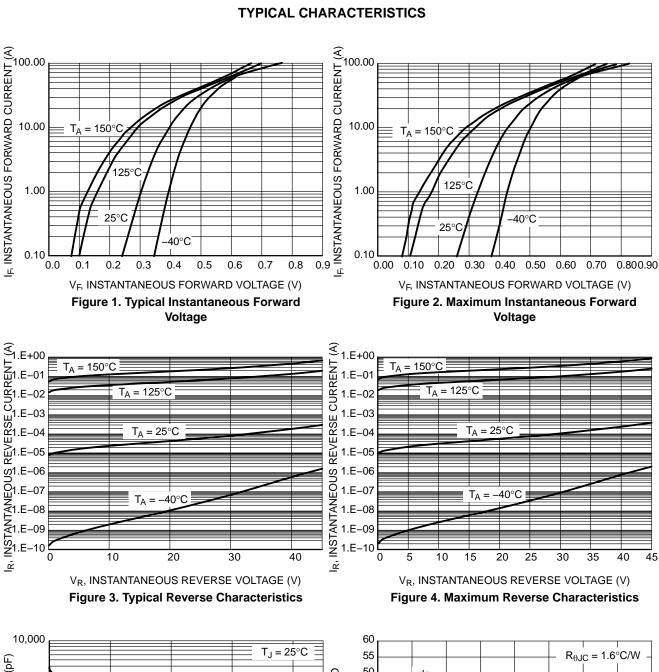
THERMAL CHARACTERISTICS

Characteristic	Symbol	Тур	Max	Unit
Thermal Resistance, Junction–to–Case, Steady State (Assumes 600 mm² 1 oz. copper bond pad, on a FR4 board)	$R_{ heta JC}$	-	1.6	°C/W
Thermal Resistance, Junction–to–Ambient, Steady State (Assumes 600 mm², 2–oz, 2 layer on a FR4 board)	$R_{ heta JA}$	-	45	°C/W

ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) $ \begin{aligned} &(i_F=15 \text{ A, } T_J=125^\circ\text{C})\\ &(i_F=15 \text{ A, } T_J=25^\circ\text{C})\\ &(i_F=30 \text{ A, } T_J=125^\circ\text{C})\\ &(i_F=30 \text{ A, } T_J=25^\circ\text{C}) \end{aligned} $	VF	0.35 0.44 0.46 0.51	0.41 0.49 0.58 0.61	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 125^{\circ}C$) (Rated dc Voltage, $T_J = 25^{\circ}C$)	i _R	200 0.3	300 0.6	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.



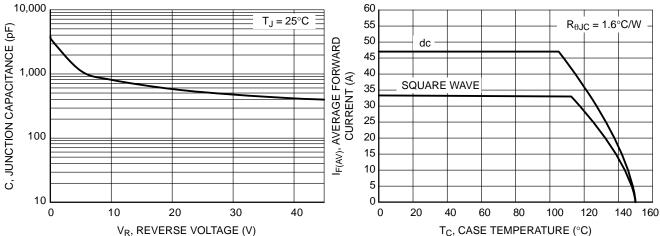
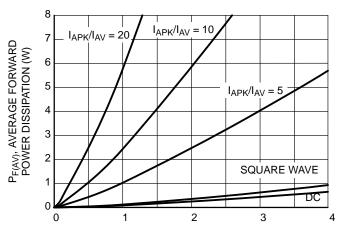


Figure 5. Typical Junction Capacitance

Figure 6. Current Derating TO-220AB

TYPICAL CHARACTERISTICS



 $I_{F(AV)}$, AVERAGE FORWARD CURRENT (A)

Figure 7. Forward Power Dissipation

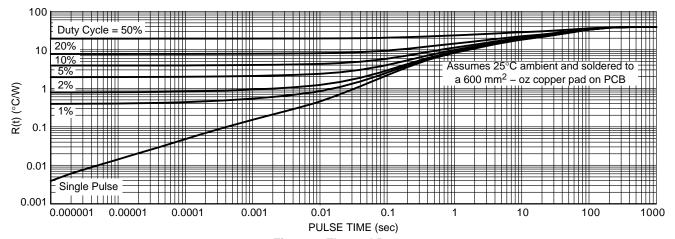
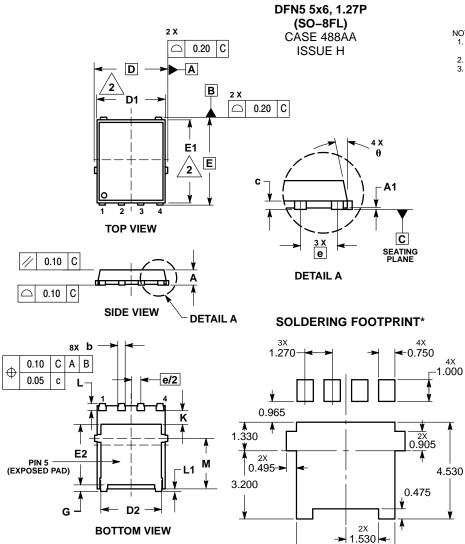


Figure 8. Thermal Response

PACKAGE DIMENSIONS



4.560 *For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.90	1.00	1.10
A1	0.00		0.05
b	0.33	0.41	0.51
С	0.23	0.28	0.33
D	5.15 BSC		
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.15 BSC		
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
е	1.27 BSC		
G	0.51	0.61	0.71
K	1.20	1.35	1.50
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0 °		12 °

STYLE 2:

- PIN 1. ANODE 2. ANODE
 - 3. ANODE
 - NO CONNECT CATHODE

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